

pending in this application. Claims 6 and 8 are the independent claims. Claims 1-5 and 7 have been cancelled to moot the Office Action's 35 U.S.C. § 102(b) rejection and objection to Claim 4. Favorable reconsideration is respectfully requested.

Applicants note with appreciation the indication that Claims 6 and 8 would be allowable if rewritten in independent form including all of the limitations of the base claim and any intervening claims. Claims 6 and 8 have been so amended and Applicants believe them in condition for allowance.

In response to the objection to Fig. 1, a substitute Fig. 1 is included herewith and incorporates the legend "PRIOR ART." Acceptance of substitute Fig. 1 is respectfully requested.

In view of the foregoing, it is respectfully submitted that the currently-pending claims clearly define statutory subject matter. Accordingly, allowance of the currently-pending claims is now respectfully submitted to be justified, and favorable consideration is earnestly solicited.

Respectfully submitted,

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APPENDIX A

MARKED-UP CLAIMS

6. (Twice Amended) A semiconductor device comprising a semiconductor body having a first region of a first conductivity type and, adjacent thereto, a second region of the second, opposite, conductivity type, a third region of the first conductivity type, which is adjacent the second region and separated from the first region by the second region, and a fourth region of the first conductivity type which is separated from the second region by the third region and which has a higher doping concentration than the third region, the first, the second and the fourth region being provided with a terminal, characterized in that the third region is provided with a protection zone of the first conductivity type having a higher doping concentration than the third region, which protection zone is separated from the second region by the third region and is situated near the fourth region, and separated from said fourth region by an intermediate, comparatively high-impedance region~~as claimed in Claim 1,~~ characterized in that the third region and the fourth region form, respectively, a drift region and a drain region of a Lateral DMOS transistor.

8. (Twice Amended) A semiconductor device comprising a semiconductor body having a first region of a first conductivity type and, adjacent thereto, a second region of the second, opposite, conductivity type, a third region of the first conductivity type, which is adjacent the second region and separated from the first region by the second region, and a fourth region of the first conductivity type which is separated from the second region by the third region and which has a higher doping concentration than the third region, the first, the second and the fourth region being provided with a terminal, characterized in that the third region is provided with a protection zone of the first conductivity type having a higher doping concentration than the third region, which protection zone is separated from the second region by the third region and is situated near the fourth region, and separated from said fourth region by an intermediate, comparatively high-impedance region~~as claimed in Claim 1,~~ characterized in that the device is of the RESURF type, wherein the product of the thickness and the doping concentration of the third region is approximately 10^{12} atoms per cm^2 .